

FOUR PROBE METHOD-I

AIM: Determination of resistivity of a semiconductor (Ge)

APPARATUS: Four Probe setup, Oven, Ge Crystal and thermometer.

DIAGRAM:

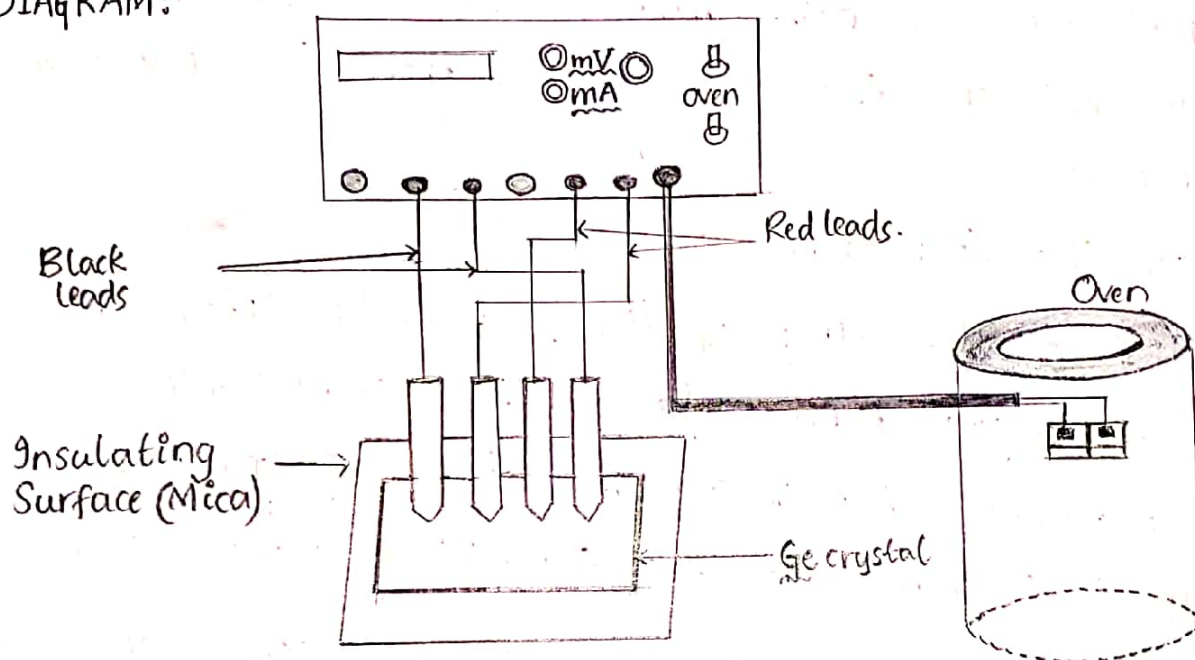


Figure 1:- EXPERIMENTAL SETUP / DIAGRAM

FORMULA:

$$\rho = \frac{V}{I} \times \frac{2\pi S}{G_T\left(\frac{W}{S}\right)}$$

Resistivity

units : Ωcm

Where, V = Potential difference between probes 2 and 3

I = Current passed through the crystal

$S = S_1 = S_2 = S_3$ = Probe spacing

$G_T\left(\frac{W}{S}\right)$ = Correction factor.

PROCEDURE:

Resistivity of Ge Crystal.

- 1) Ensure that the Ge Crystal is placed on the base plate of the four probe arrangement and the four probes rest in the middle of the Ge Crystal.
- 2) Connect the outer pair of probes to the constant current terminals and the inner pair of probes to the voltage terminals.
- 3) Place the four probe arrangement in the oven.
- 4) Switch on the Supply of the four probe setup and put the digital panel meter in the current measuring mode with the help of selector switch. Adjust the current to 2 mA. Now put the digital panel meter in the voltage measuring mode and note down the voltage.
- 5) Change the current in intervals of 1 mA starting from 2 mA up to 10 mA and note down the corresponding voltages in the given table.
- 6) Using the given formula, the average resistivity of the Ge crystal at room temperature is to be calculated.

OBSERVATIONS:

RESISTIVITY OF Ge CRYSTAL.

Room temperature (RT) =

Probe spacing $S = 0.2 \text{ cm}$, Correction factor for the given
Crystal $G_T \left(\frac{W}{S} \right) = 5.89$

S.No.	CURRENT (mA)	VOLTAGE (mV)	RESISTIVITY ($\Omega \text{ cm}$)	AVERAGE RESISTIVITY ($\Omega \text{ cm}$)
1	2	102	10.86	10.989
2	3	153	10.863	
3	4	205	10.916	
4	5	258	10.991	
5	6	310	11.005	
6	7	362	11.015	
7	8	416	11.076	
8	9	469	11.099	
9	10	520	11.076	

CALCULATIONS:

Room Temperature (RT) = 30°C , Probe Spacing $S = 0.2 \text{ cm}$ Correction factor for the given crystal $G_T \left(\frac{W}{S} \right) = 5.89$

$$\rho = \frac{V}{I} \times \frac{2\pi S}{G_T \left(\frac{W}{S} \right)}$$

$$\Rightarrow \frac{2\pi S}{G_T \left(\frac{W}{S} \right)} = \frac{2\pi \times 0.2}{5.89} = 0.213$$

$$1.) \therefore \rho = \frac{102}{2} \times 0.213 = 10.86 \Omega \text{ cm}$$

$$2.) \rho = \frac{153}{3} \times 0.213 = 10.863 \Omega \text{ cm}$$

$$3) \rho = \frac{205}{4} \times 0.213 = 10.916 \, \Omega \text{ cm}$$

⋮

PRECAUTIONS:

- 1.) Do not apply pressure on the electrical contacts to the Ge crystal as it is very brittle.
- 2.) Ensure that the oven is OFF.

RESULT:

Resistivity of the Given Ge crystal at room temperature is found to be $10.989 \, \Omega \text{ cm}$.